



General Description:

- (1) Chip Dimension
 Chip Size= 11.6 mil x 11.6 mil (290um x 290um)
 Chip Thickness= 90±10μm
 Bonding Pad= 85±5μm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V _F	2.8	-	3.5	V	I _F =20mA
Dominant Wavelength	λ _D	445	-	475	nm	I _F =20mA
Reverse Current	I _R	0	-	1	μA	V _R =-5V

Luminous Intensity (I _v),mcd at I _F =20mA	Dominant Wavelength(nm)												
	Range	445~447.5	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465	465~467.5	467.5~470	470~472.5	472.5~475
50~60	*												
60~70	*	*	*										
70~80	*	*	*	*									
80~90	*	*	*	*	*								
90~100		*	*	*	*	*	*	*					
100~120				*	*	*	*	*	*	*			
120~140					*	*	*	*	*	*	*	*	*
140~160						*	*	*	*	*	*	*	*
160~180							*	*	*	*	*	*	*
180~200								*	*	*	*	*	*

Features:

- 1. High Luminous Intensity
- 2. Long Operation Life
- 3. High Current; Pulse Operation
- 4. Indoor/Outdoor Applications

Notes:

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error of ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD

